

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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TAN 350

350 Watts, 50 Volts, Pulsed Avionics 960 – 1215 MHz

GENERAL DESCRIPTION

The **TAN350** is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 960-1215 MHz. The device has gold thin-film metallization and diffused ballasting for proven highest MTTF. The transistor includes input and output prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

CASE OUTLINE 55ST Style 1

ABSOLUTE MAXIMUM RATINGS

Power Dissipation

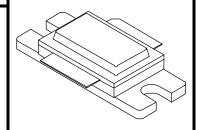
Device Dissipation @25°C (P_d) 1450 W (At rated pulse condition)

Voltage and Current

 $\begin{array}{lll} \mbox{Collector to Base Voltage } (\mbox{BV}_{ces}) & \mbox{65 V} \\ \mbox{Emitter to Base Voltage } (\mbox{BV}_{ebo}) & \mbox{2.0 V} \\ \mbox{Collector Current } (\mbox{I}_c) & \mbox{40 A} \\ \end{array}$

Temperatures

Storage Temperature -65 to +200 °C Operating Junction Temperature +230 °C



ELECTRICAL CHARACTERISTICS @ 25°C

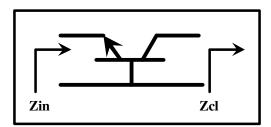
SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P _{out}	Power Out	F = 960 - 1215 MHz	350			W
P_{in}	Power Input	$V_{CC} = 50 \text{ Volts}$			70	W
P_{g}	Power Gain	$PW = 10 \mu sec$	7.0	7.5		dB
η_c	Collector Efficiency	DF = 10%	38	40		%
VSWR	Load Mismatch Tolerance	F = 1090 MHz	3:1			

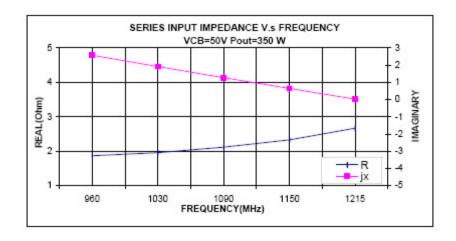
FUNCTIONAL CHARACTERISTICS @ 25°C

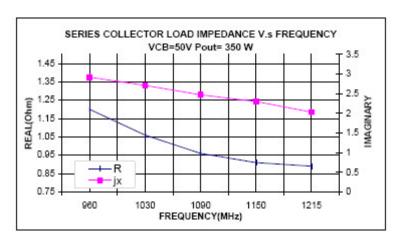
BV_{ebo}	Emitter to Base Breakdown	Ie = 25 mA	2.0		V
BV_{ces}	Collector to Emitter Breakdown	Ic = 50 mA	65		V
h_{FE}	DC – Current Gain	Ic = 1A, Vce = 5V	10		
θjc^2	Thermal Resistance			.12	°C/W

Rev A - Sept. 2005

	Zin		ZCL	
Frequency	R	jx	R	jx
960	1.87	2.58	1.2	2.92
1030	1.96	1.92	1.06	2.71
1090	2.12	1.27	0.96	2.47
1150	2.33	0.65	0.91	2.3
1215	2.67	0.03	0.89	2.03







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